AF70N03

N-Channel Enhancement Mode Power MOSFET

■ Features

-Low Gate Charge
-Simple Drive Requirement
-Fast Switching
-RoHS Compliant
-Pb Free Plating Product

■ General Description

The advanced power MOSFET provides the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

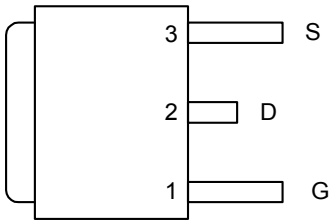
The TO-252 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

■ Product Summary

BV_{DSS} (V)	$R_{DS(ON)}$ (mΩ)	I_D (A)
30	9	60

■ Pin Assignments

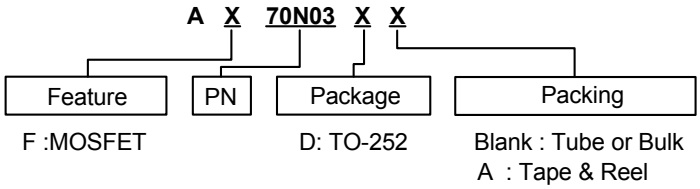
(Front View)



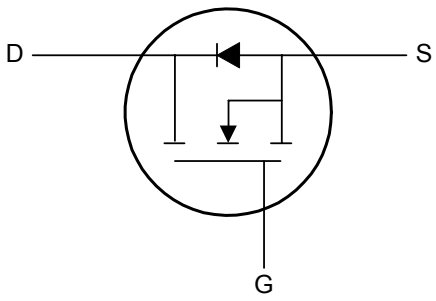
■ Pin Descriptions

Pin Name	Description
S	Source
G	Gate
D	Drain

■ Ordering information



■ Block Diagram



This datasheet contains new product information. Anachip Corp. reserves the rights to modify the product specification without notice. No liability is assumed as a result of the use of this product. No rights under any patent accompany the sale of the product.

■ Absolute Maximum Ratings

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current, V_{GS}=10V	T_A=25ºC	60	A
		T_A=100ºC	43	
I_{DM}	Pulsed Drain Current **(Note 1)**		195	A
P_D	Total Power Dissipation	T_A=25ºC	53	W
	Linear Derating Factor		0.36	W/ºC
T_{STG}	Storage Temperature Range		-55 to 175	ºC
T_J	Operating Junction Temperature Range		-55 to 175	ºC

■ Thermal Data

Symbol	Parameter		Maximum	Units
$R_{\theta JC}$	Thermal Resistance Junction-Case	Max.	2.8	ºC/W
$R_{\theta JA}$	Thermal Resistance Junction- Ambient	Max.	110	ºC/W

■ Electrical Characteristics (T_J=25ºC unless otherwise noted)

Symbol	Parameter	Test Conditions	Limits			Unit
			Min.	Typ.	Max.	
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	30	-	-	V
$\triangle BV_{DSS}/\triangle T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25ºC, I_D=1mA	-	0.032	-	V/ºC
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=33A	-	-	9	mΩ
		V_{GS}=4.5V, I_D=20A	-	-	18	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D=250uA	1	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=33A	-	35	-	S
I_{DSS}	Drain-Source Leakage Current(T_J=25ºC)	V_{DS}=30V, V_{GS}=0V	-	-	1	uA
	Drain-Source Leakage Current(T_J=175ºC)	V_{DS}=24V, V_{GS}=0V	-	-	250	
I_{GSS}	Gate Source Leakage	V_{GS}=±20V	-	-	±100	nA
Q_g	Total Gate Charge **(Note 2)**	I_D=33A, V_{DS}=20V, V_{GS}=4.5V	-	16.5	-	nC
Q_{gs}	Gate-Source Charge		-	5	-	
Q_{gd}	Gate-Drain ("Miller") Charge		-	10.3	-	
$t_{d(on)}$	Turn-On Delay Time **(Note 2)**	V_{DS}=15V, I_D=33A, R_G=3.3Ω, V_{GS}=10V, R_D=0.45Ω	-	8.2	-	nS
t_r	Rise Time		-	105	-	
$t_{d(off)}$	Turn-Off Delay Time		-	21.4	-	
t_f	Fall-Time		-	8.5	-	
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, f=1.0MHz	-	1485	-	pF
C_{oss}	Output Capacitance		-	245	-	
C_{rss}	Reverse Transfer Capacitance		-	170	-	

■ Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current (Body Diode)	V_D=V_G=0V, V_S=1.3V	-	-	60	A
I_{SM}	Pulsed Source Current (Body Diode) **(Note 1)**		-	-	195	A
V_{SD}	Forward On Voltage **(Note 2)**	T_J=25ºC, I_S=60A, V_{GS}=0V	-	-	1.3	V

Note 1: Pulse width limited by safe operating area.
Note 2: Pulse width ≤ 300us, duty cycle ≤ 2%.

■ Typical Performance Characteristics

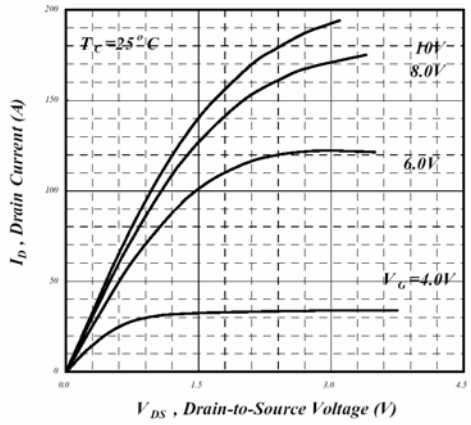


Fig 1. Typical Output Characteristics

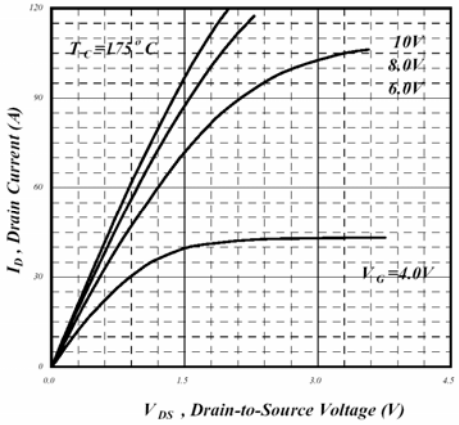


Fig 2. Typical Output Characteristics

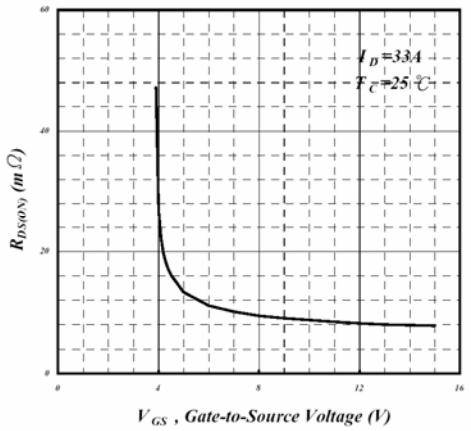


Fig 3. On-Resistance v.s. Gate Voltage

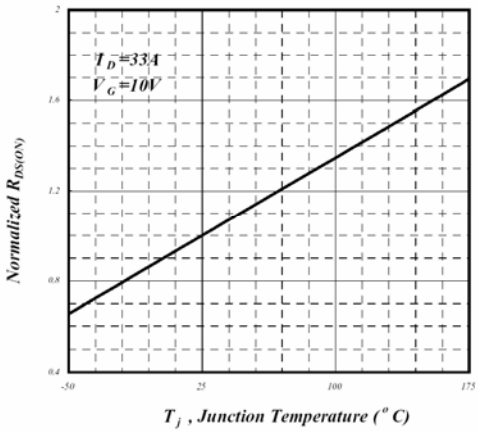


Fig 4. Normalized On-Resistance v.s. Junction Temperature

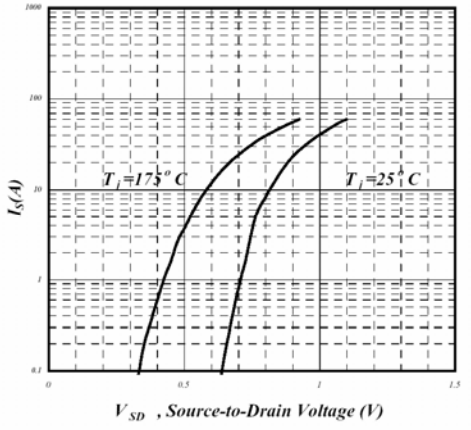


Fig 5. Forward Characteristic of Reverse Diode

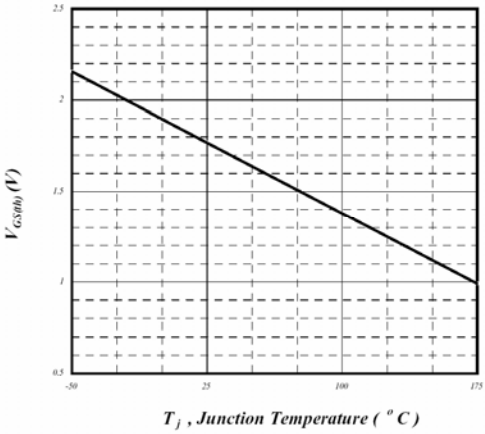


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

■ Typical Performance Characteristics

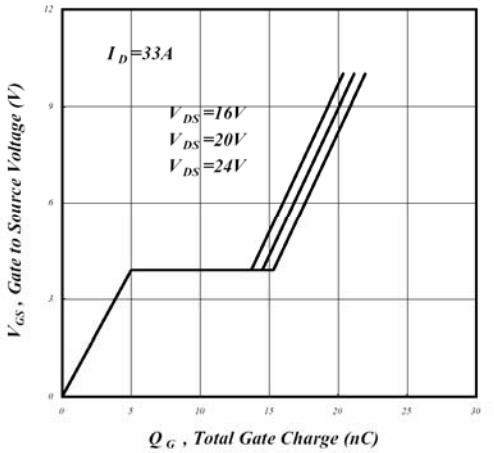


Fig 9. Gate Charge Characteristics

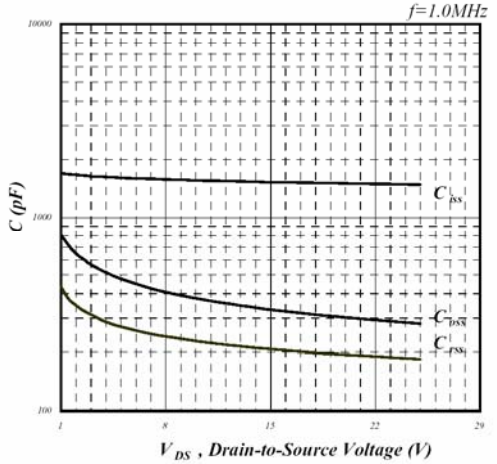


Fig 10. Typical Capacitance Characteristics

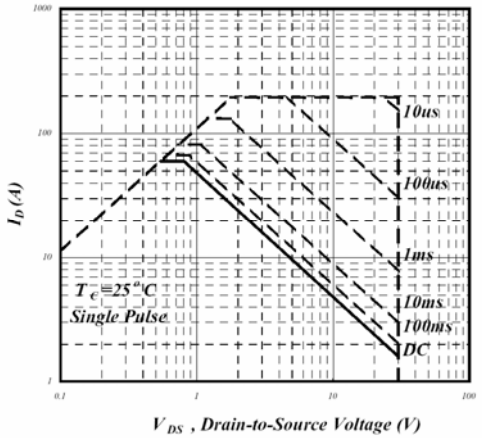


Fig 7. Maximum Safe Operating Area

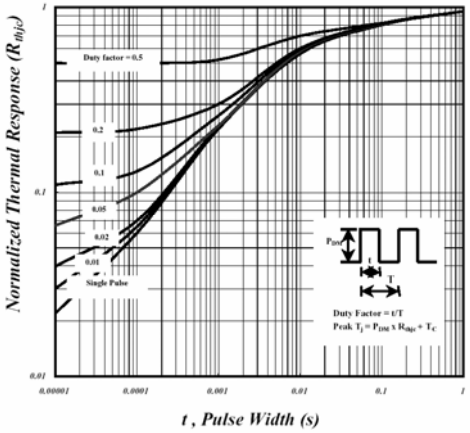


Fig 8. Effective Transient Thermal Impedance

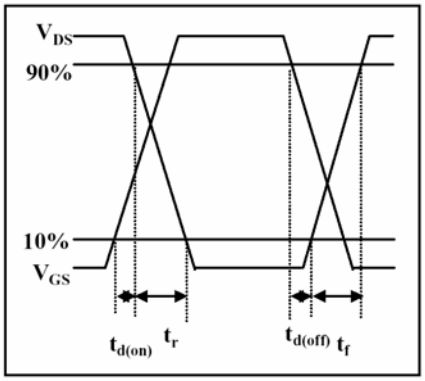


Fig 11. Switching Time Waveform

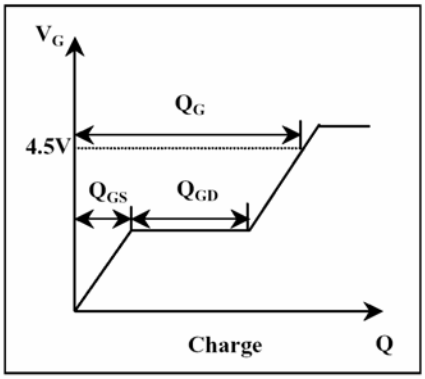
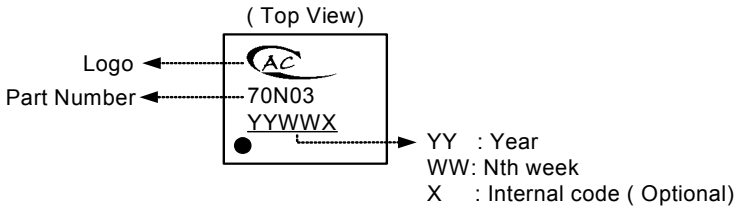


Fig 12. Gate Charge Waveform

N-Channel Enhancement Mode Power MOSFET

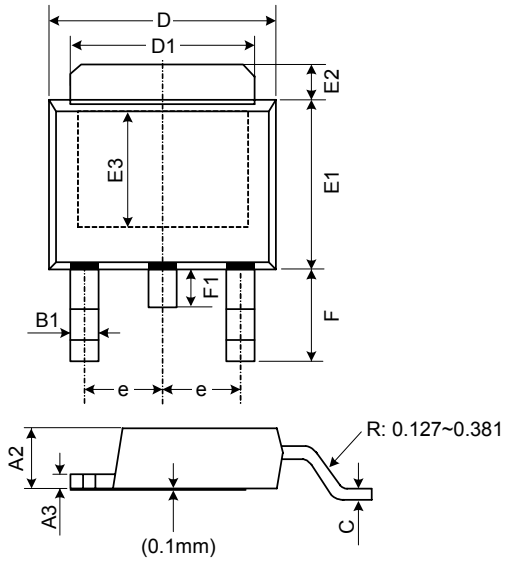
■ Marking Information

TO-252



■ Package Information

Package Type: TO-252



1. All Dimensions Are in Millimeters.
2. Dimension Does Not Include Mold Protrusions.

Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
F	2.20	2.63	3.05
F1	0.50	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.70
E3	3.50	4.00	4.50
e	-	2.30	-
C	0.35	0.50	0.65